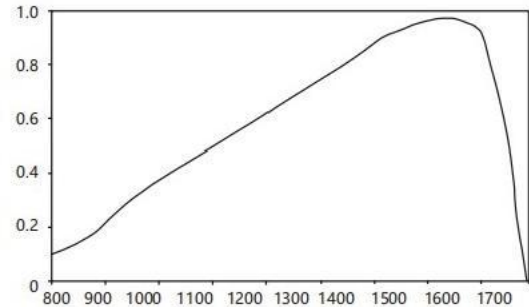


InGaAs APD ($\Phi 80\mu\text{m}$)

CTAPD80V1

Application

- Distance measurement
- Spatial light transmission
- OTDR
- Low-light-level detection



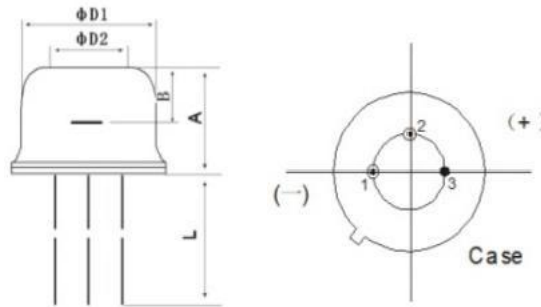
Typical response curve graph

1. Parameter

Electro-Optical Characteristics (@ $T_c=22\pm 3^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ.	Max.	Unit
Response Spectrum	λ		950~1700			nm
Responsivity	Re	$\lambda=1550\text{nm}$ $P_{in}=1\mu\text{W}, M=1$	0.90	1.05	—	AW
Multiplication factor	M	$\lambda=1550\text{nm}$ $P_{in}=1\mu\text{W}, V_r=V_{BR}-2\text{V}$	10.00			
Dark Current	I _b	$V_R=V_{BR}-2\text{V}$ $P_{in}=0\mu\text{W}$		16.00	50.00	nA
-3dB cut-off frequency	BW	M=10 $R_L=50\Omega$	2.5	—	—	GHz
Reverse Breakdown Voltage	V _{BR}	$I_R=10\mu\text{A}, P_{in}=0\mu\text{W}$	40.0		50.00	V
Capacitance	C	$V_R=V_{BR}-2\text{V}, f=1\text{MHz}$	—	0.38	0.50	pF
Temperature coefficient of V _{BR}	Y	$I_R=10\mu\text{A}, P_{in}=0\mu\text{W}$ $-55^\circ\text{C}\sim+85^\circ\text{C}$	0.03	0.08	0.13	V/°C

2. Package Drawings



	CTAPD8OV1
PIN1	Cathode
PIN2	Gnd
PIN3	Anode

Symbol	Min	Typ	Max	Units
$\phi D1$	4.65	4.70	4.80	mm
A	3.15	3.25	3.4	mm
B	1.47	1.5	1.53	mm
L	13.5	15.0	18	mm